

Revision 1.11

GAIN CHIPS AR coated Fabry-Perot Laser



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Contact us

General Product Information

Product	Application
tunable 740 nm Fabry-Perot Laser	Spectroscopy
for use in an External Cavity Diode Laser (ECDL)	covering wavelengths between 723 and 742 nm
sealed SOT Housing	
Monitor Diode	



Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-40		85
Operational Temperature at Case	T_{C}	°C	-20		50
Forward Current	I _F	mA			180
Reverse Voltage	V_R	V			2
Output Power (extracavity)	P_{opt}	mW			50

Measurement Conditions / Comments

Stess in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _C	°C	15		40
Forward Current	I _F	mA			160

Measurement Conditions / Comments

Characteristics ex-cavity at T_C= 25°C, at BOL under recommended working condition

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm		735	
Tuning Range	$\Delta \lambda_{\text{tun}}$	nm	723		742
Output Power	P _{opt}	mW		40	
Polarization				TM	
Spatial Mode (transversal)				TEM ₀₀	

Measurement Conditions / Comments

The actual achieved wavelength and power are strongly influenced by the external cavity. eyP gives no guarantee on these parameters.

E field perpendicular to Pin 2 - Pin 3 - plane Fundamental Mode



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Amplified Spontaneous Emission (ASE) without external cavity

Parameter	Symbol	Unit	min	typ	max
Divergence parallel (FWHM)	$\Theta_{ }$			10	
Divergence perpendicular (FWHM)	Θ_{\perp}			28	
Monitor Detector Responsivity	I _{mon} / P _{ASE} μ	A/mW	1		40

Measurement Conditions / Comments
parallel to Pin 2 - Pin 3 plane (see p. 3)
perpendicular to Pin 2 - Pin 3 plane (see p. 3)
$U_{R MD} = 5 V$

Chip Parameter

Parameter	Symbol	Unit	min	typ	max
Cavity Length	L	μm		1500	
Reflectivity at Front Facet	R_{ff}			3·10 ⁻⁴	1·10 ⁻³

Measurement Conditions / Comments	



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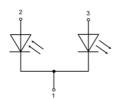
Package Dimensions

Parameter	Symbol	Unit	min	typ	max
Height of Emission Plane	h	mm	3.50	3.65	3.70
Excentricity of Emission Center	R	mm			0.12
Pin Length	L_{PIN}	mm		14	

Measurement Conditions / Comments
reference plane: top side of TO header
reference: center of outer diameter of header

Package Pinout

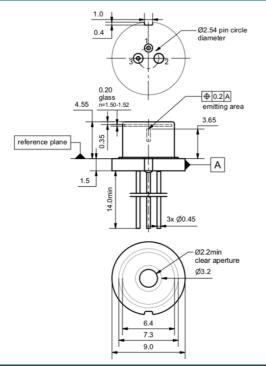
- 1 Laser Diode Cathode, Monitor Diode Cathode, Case
- 2 Photo Diode Anode
- 3 Laser Diode Anode



AIZ-16-0421-1517



Package Drawings





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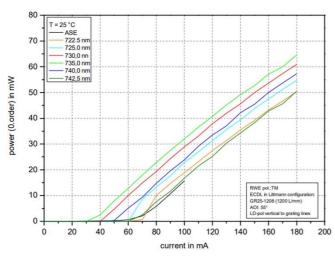


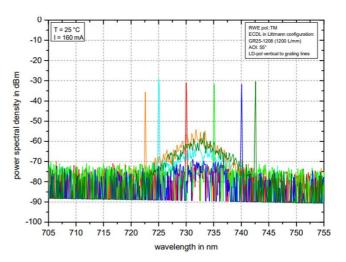
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Typical Measurement Results ex-cavity





Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The TPA diode type is known to be sensitive against thermal stress. It should not be operated without appropriate injection from a seed laser. Operating at moderate temperatures on proper heat sinks willl contribute to a long lifetime of the diode. The chip should be protected against moisture. A water vapor content below 5000 ppm is recommended for applications with high reliability requirements.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.







INVISIBLE LASER RADIATION
AVOID EYE OR SKIN EXPOSURE
TO DIRECT OR SCATTERED RADIATION
CLASS 4 LASER PRODUCT
WAVELENGTH 735 nm
MAX. OUTPUT POWER 25 mW

IEC-60825-0







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